



# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





# BUJ302AD

NPN power transistor

Rev. 01 — 28 March 2011

Product data sheet

## 1. Product profile

### 1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT428 (DPAK) surface mounted package.

### 1.2 Features and benefits

- Fast switching
- High voltage capability
- Low thermal resistance
- Surface-mountable package

### 1.3 Applications

- DC-to-DC converters
- High-frequency electronic lighting ballast applications
- Inverters
- Motor control systems

### 1.4 Quick reference data

Table 1. Quick reference data

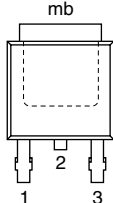
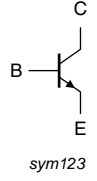
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_C$	collector current	see <a href="#">Figure 1</a> ; see <a href="#">Figure 2</a> ; see <a href="#">Figure 4</a>	-	-	4	A
$P_{tot}$	total power dissipation	$T_{mb} \leq 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	-	80	W
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	-	1050	V
<b>Static characteristics</b>						
$h_{FE}$	DC current gain	$I_C = 0.1\text{ A}$ ; $V_{CE} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 11</a>	[1]	48	66	100
		$I_C = 0.8\text{ A}$ ; $V_{CE} = 3\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 12</a>	[1]	25	42	50

[1] Pulse test: pulse duration  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$



## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base		
2	C	collector <sup>[1]</sup>		
3	E	emitter		
mb	C	mounting base; connected to collector		

**SOT428 (DPAK)**

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

## 3. Ordering information

**Table 3. Ordering information**

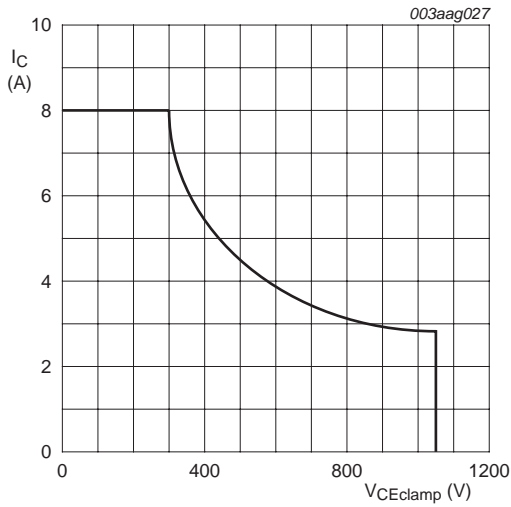
Type number	Package		Version
	Name	Description	
BUJ302AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

## 4. Limiting values

**Table 4. Limiting values**

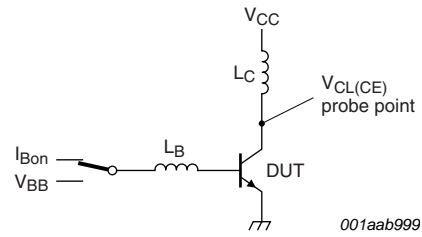
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CESM}$	collector-emitter peak voltage	$V_{BE} = 0\text{ V}$	-	1050	V
$V_{CEO}$	collector-emitter voltage	$I_B = 0\text{ A}$	-	400	V
$I_C$	collector current	see <a href="#">Figure 1</a> ; see <a href="#">Figure 2</a> ; see <a href="#">Figure 4</a>	-	4	A
$I_{CM}$	peak collector current		-	8	A
$I_B$	base current		-	2	A
$I_{BM}$	peak base current		-	4	A
$P_{tot}$	total power dissipation	$T_{mb} \leq 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	80	W
$T_{stg}$	storage temperature		-65	150	°C
$T_j$	junction temperature		-	150	°C
$V_{EBO}$	emitter-base voltage	$I_C = 0\text{ A}$ ; $I_E = 2\text{ A}$ ; $t_p < 10\text{ ms}$	-	24	V



$$T_j \leq T_{j(max)} \text{ } ^\circ\text{C}$$

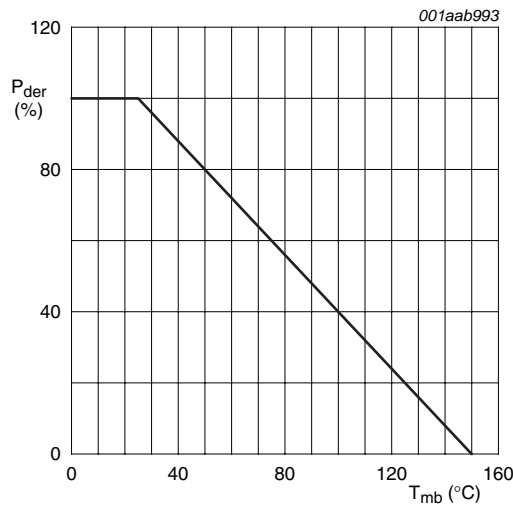
**Fig 1. Reverse bias safe operating area**



$$V_{CL(CE)} \leq 1000 \text{ V}; V_{CC} = 150 \text{ V}; V_{BB} = -5 \text{ V};$$

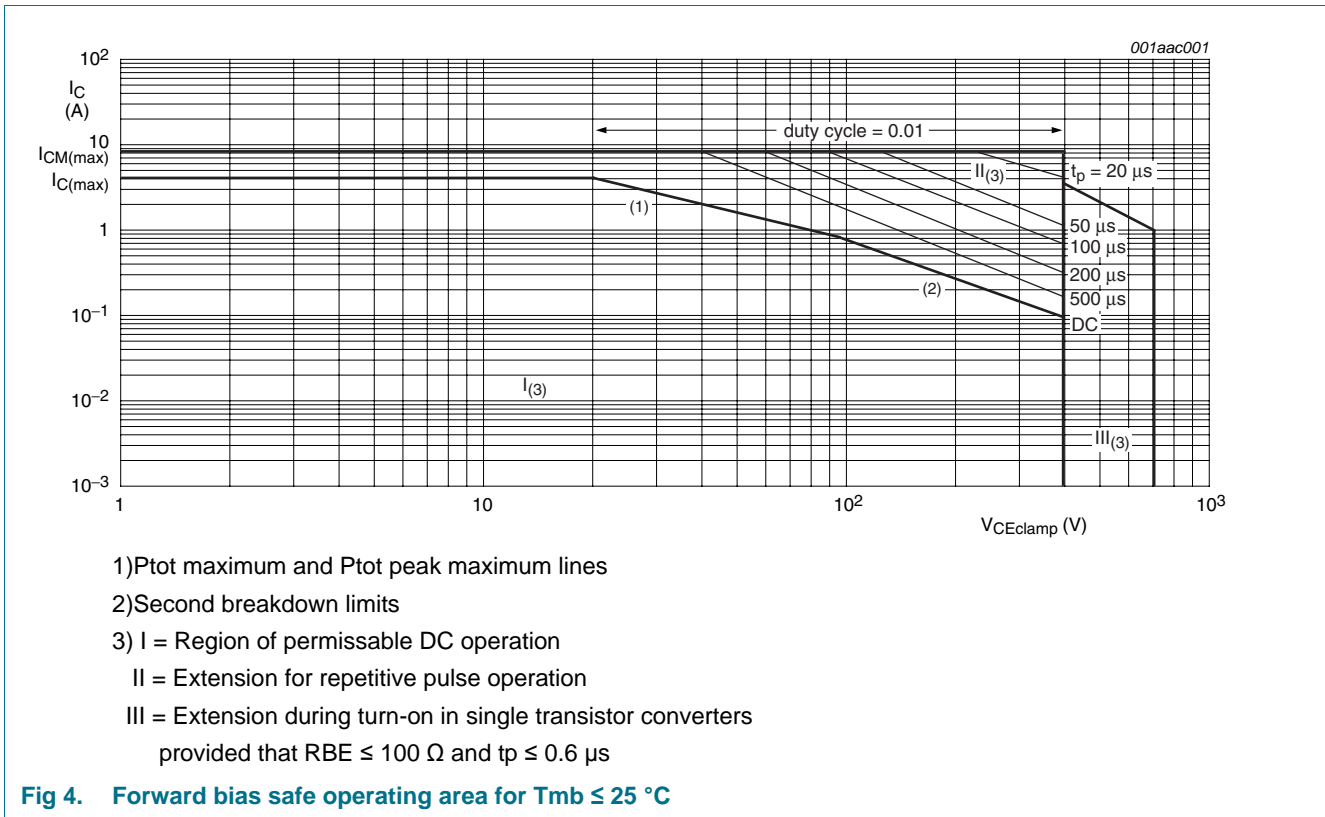
$$L_B = 1 \mu\text{H}; L_C = 200 \mu\text{H}$$

**Fig 2. Test circuit for reverse bias safe operating area**



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100 \%$$

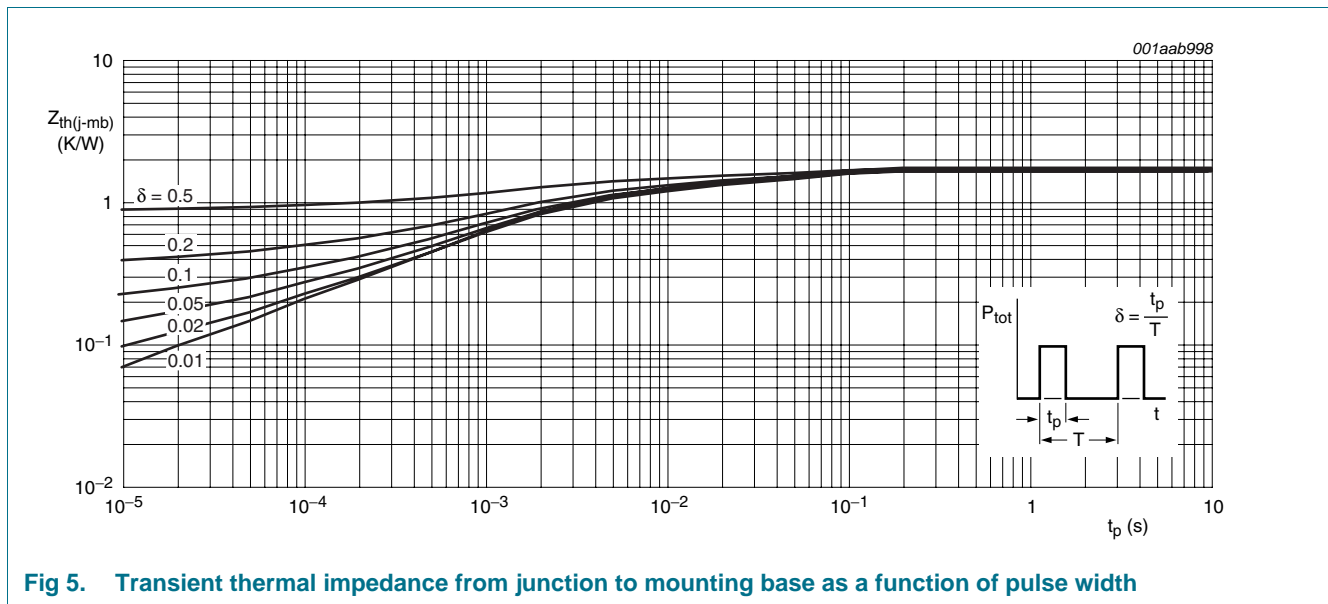
**Fig 3. Normalized total power dissipation as a function of mounting base temperature**



## 5. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 5</a>	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient in free air		-	60	-	K/W



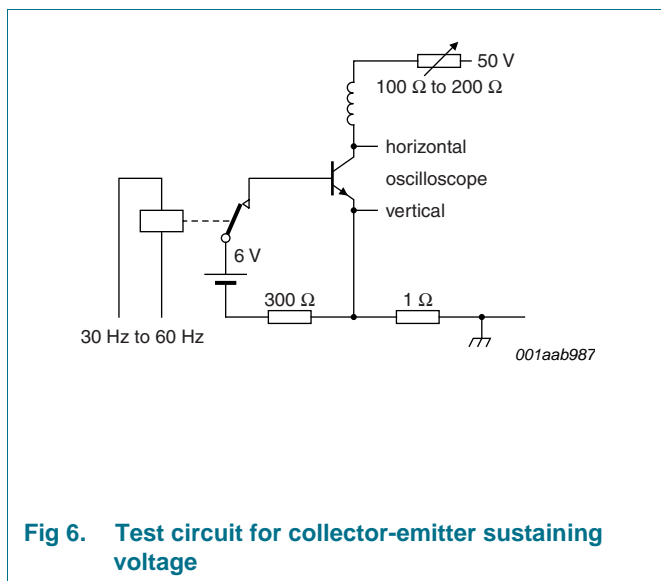
**Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse width**

## 6. Characteristics

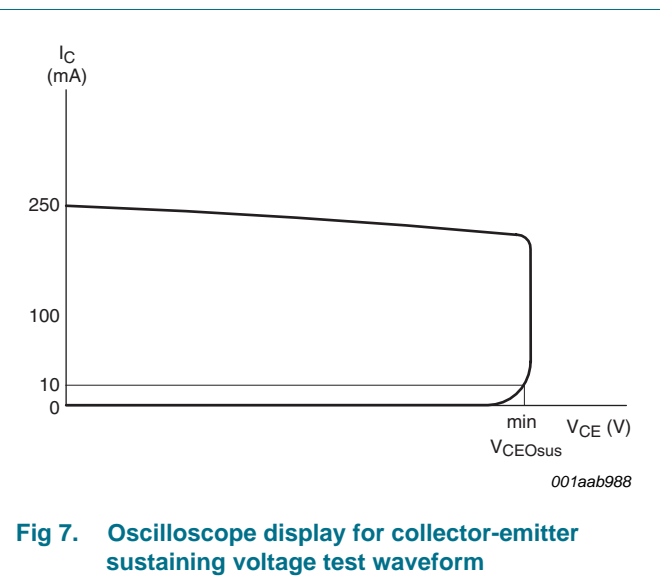
**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Static characteristics</b>							
$I_{CES}$	collector-emitter cut-off current	$V_{BE} = 0\text{ V}; V_{CE} = 1050\text{ V}; T_{mb} = 25\text{ }^\circ\text{C}$	-	0.2	10	$\mu\text{A}$	
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 400\text{ V}; I_B = 0\text{ A}; T_{mb} = 25\text{ }^\circ\text{C}$	-	10	250	mA	
$V_{(BR)EBO}$	open-collector emitter-base breakdown voltage	$I_B = 1\text{ mA}; I_C = 0\text{ A}; T_{mb} = 25\text{ }^\circ\text{C}$	15	19	-	V	
$V_{CE0sus}$	collector-emitter sustaining voltage	$I_B = 0\text{ A}; I_C = 10\text{ mA}; L_C = 25\text{ mH}; T_{mb} = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 6</a> ; see <a href="#">Figure 7</a>	[1]	400	470	V	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 0.2\text{ A}; T_{mb} = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 8</a> ; see <a href="#">Figure 9</a>	[1]	-	0.15	0.5	V
		$I_C = 3.5\text{ A}; I_B = 1\text{ A}; T_{mb} = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 8</a> ; see <a href="#">Figure 9</a>	[1]	-	0.6	1.5	V
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 3.5\text{ A}; I_B = 1\text{ A}; T_{mb} = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 10</a>	[1]	-	1.1	1.5	V
$h_{FE}$	DC current gain	$I_C = 0.1\text{ A}; V_{CE} = 5\text{ V}; T_{mb} = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 11</a>	[1]	48	66	100	
		$I_C = 0.8\text{ A}; V_{CE} = 3\text{ V}; T_{mb} = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	[1]	25	42	50	
<b>Dynamic characteristics</b>							
$t_s$	storage time	$I_C = 2.5\text{ A}; I_{B0n} = 0.5\text{ A}; I_{B0f} = -0.5\text{ A};$	-	-	3.5	$\mu\text{s}$	
$t_f$	fall time	$R_L = 60\text{ }\Omega; V_{BB} = -5\text{ V}; T_{mb} = 25\text{ }^\circ\text{C};$ resistive load; $t_p = 300\text{ }\mu\text{s};$ see <a href="#">Figure 13</a> ; see <a href="#">Figure 14</a>	-	-	500	ns	

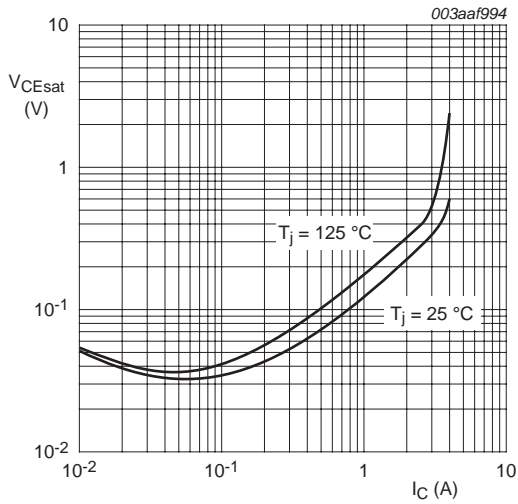
[1] Pulse test: pulse duration  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$



**Fig 6. Test circuit for collector-emitter sustaining voltage**

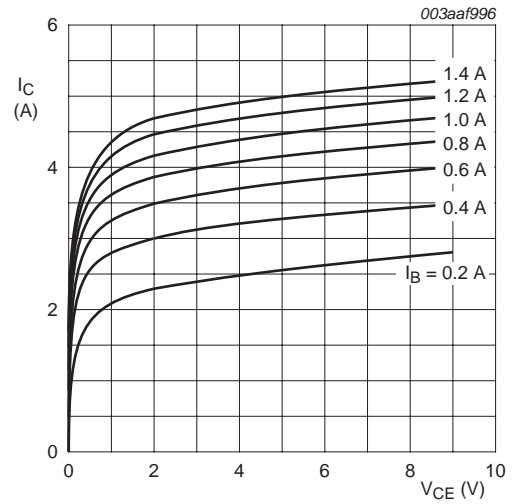


**Fig 7. Oscilloscope display for collector-emitter sustaining voltage test waveform**

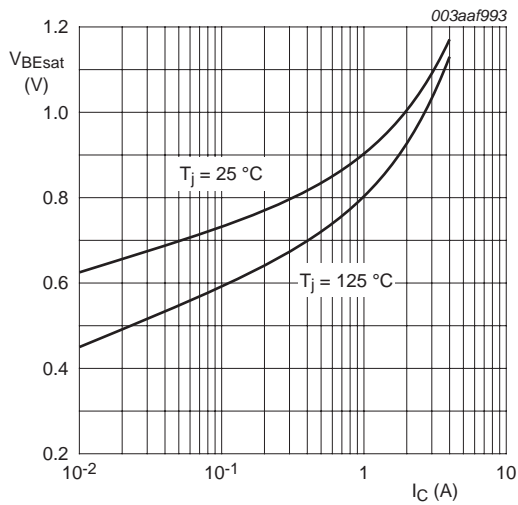


$$I_C / I_B = 3$$

**Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values**

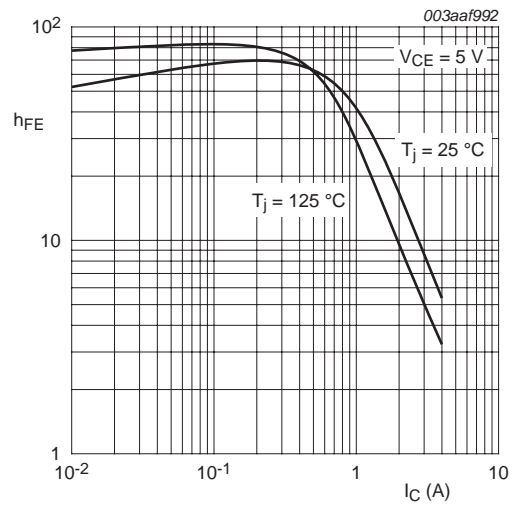


**Fig 9. Collector current as a function of collector-emitter voltage; typical values**



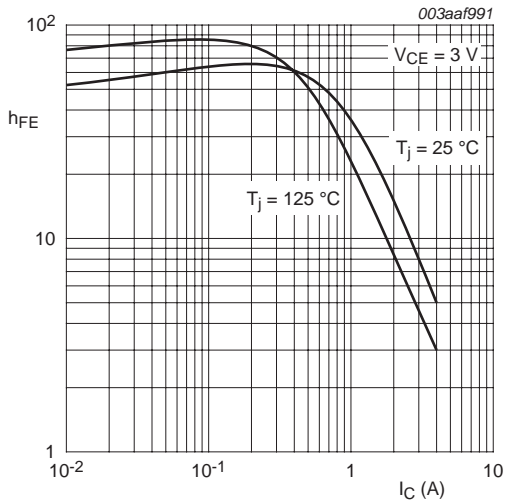
$$I_C / I_B = 3$$

**Fig 10. Base-emitter saturation voltage as a function of collector current; typical values**

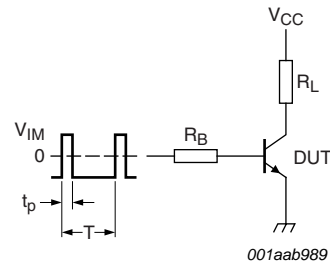


**Fig 11. DC current gain as a function of collector current; typical values**



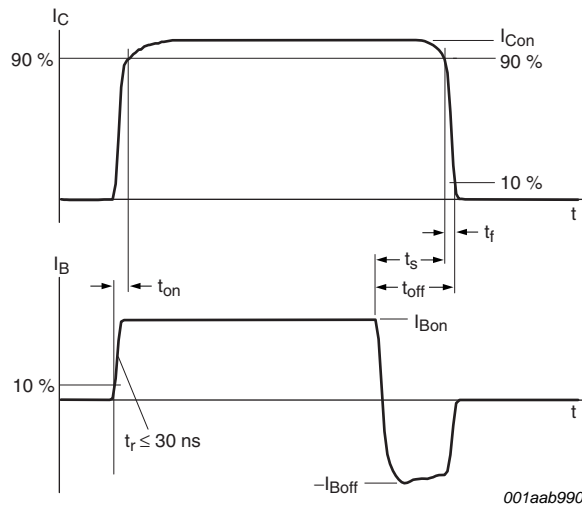


**Fig 12. DC current gain as a function of collector current; typical values**



$V_{IM} = -6 \text{ to } +8 \text{ V}; V_{CC} = 250 \text{ V}; t_p = 20 \mu\text{s}; \delta = \frac{t_p}{T} = 0.01$   
 $R_B$  and  $R_L$  calculated from  $I_{Con}$  and  $I_{Bon}$  requirements.

**Fig 13. Test circuit for resistive load switching**



**Fig 14. Switching times waveforms for resistive load**

## 7. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428

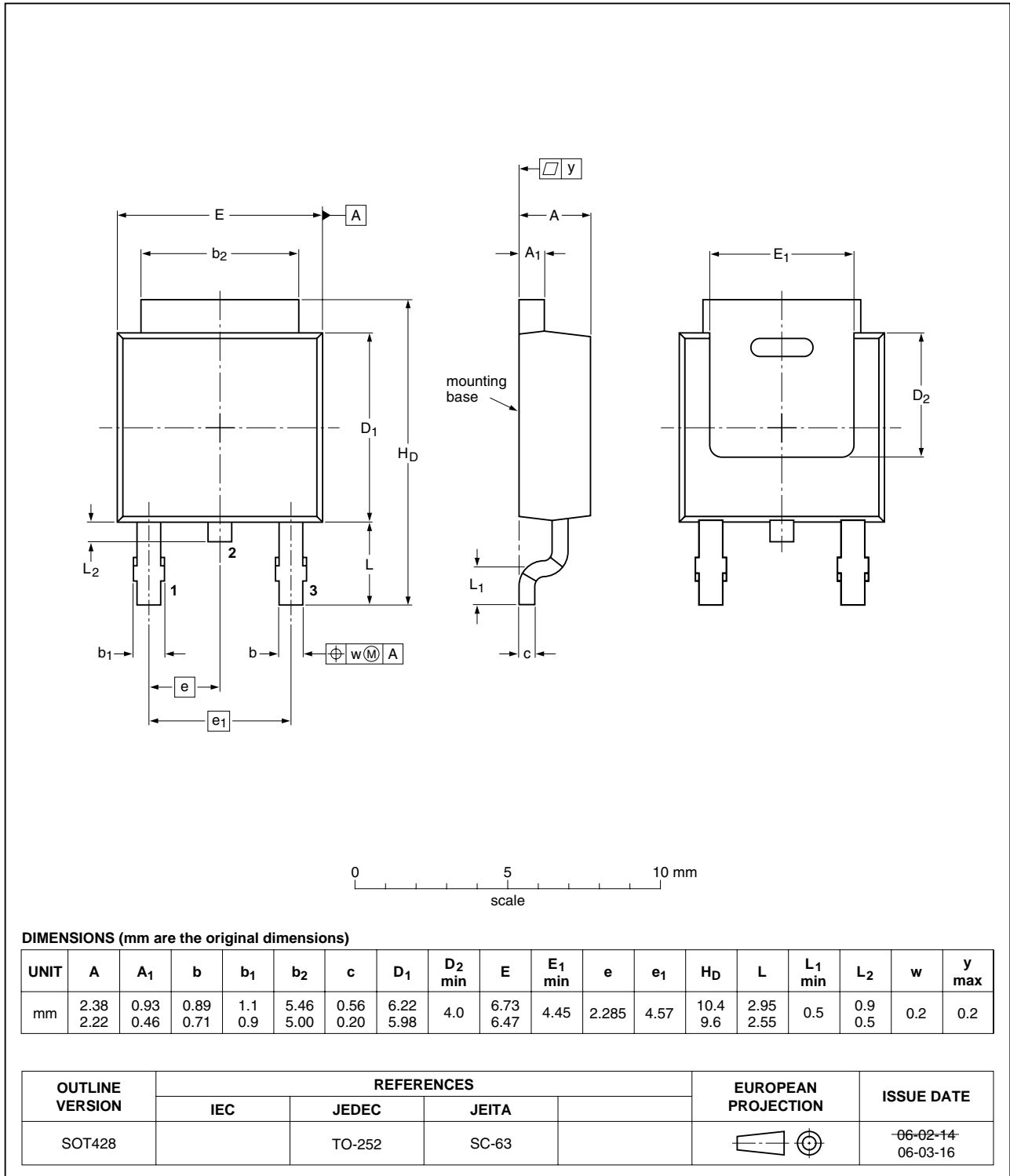
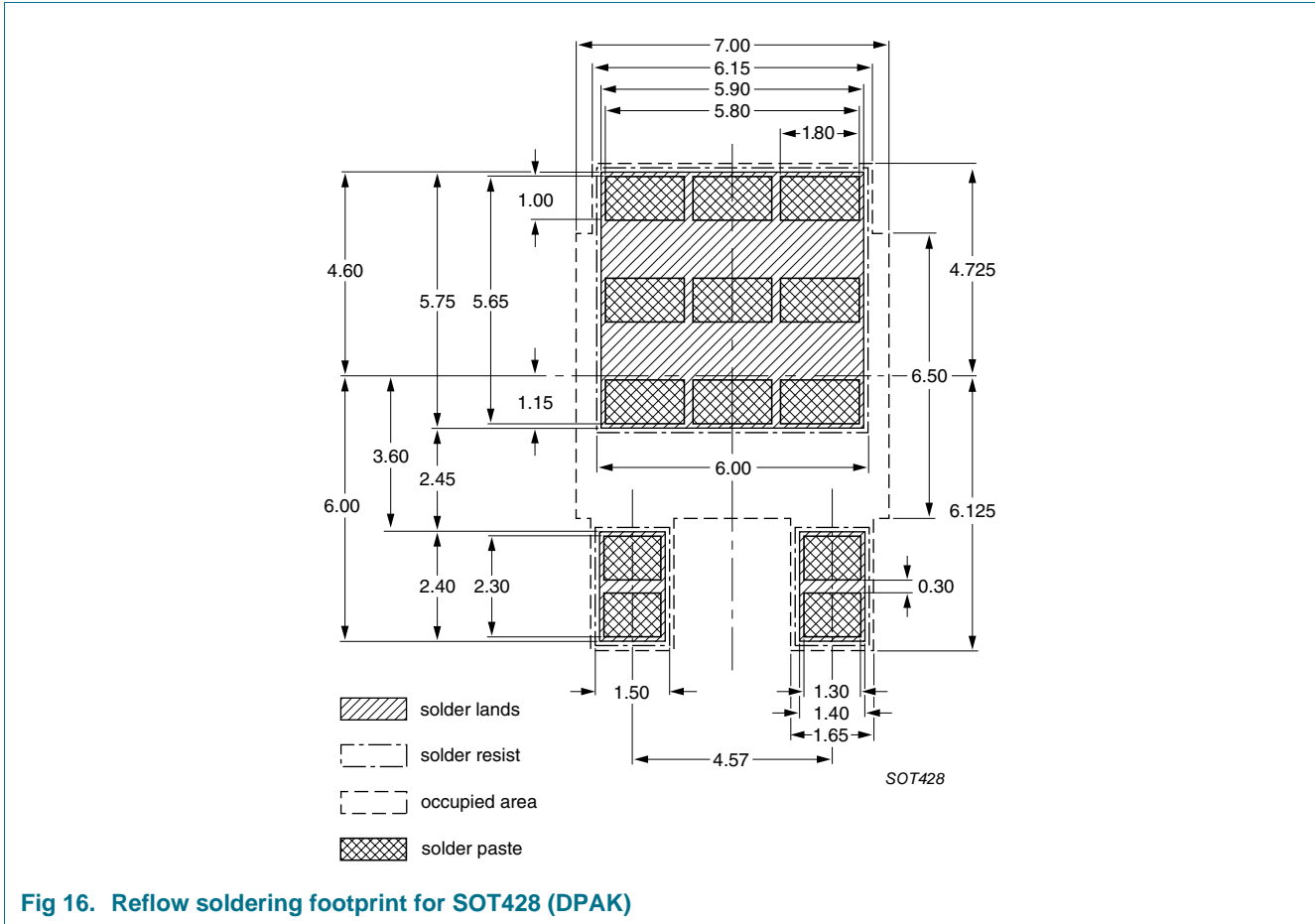


Fig 15. Package outline SOT428 (DPAK)

**8. Soldering**



## 9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJ302AD v.1	20110328	Product data sheet	-	-

## 10. Legal information

### 10.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Date of release: 28 March 2011

Document identifier: BUJ302AD